

# YJ Planar Schottky Barrier Diode Die Specification

200V 1A, 32mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB032H200SS-280A

## Main Products Characteristics

- Average forward current:  $I_F(AV) = 1 \text{ A}$
- Maximum operating junction temperature:  $T_j = 175 \text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

## Maximum Ratings

## Static Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

$I_F = 1 \text{ A}$

Pulse Test:  $t_p = 300 \mu\text{s}$ , 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 \* : Also can offer device with 8 mils thickness

2 \*\*: Cutting street width is around 1.5 mils

## Important Notice